

GRAPHENE MECHANICAL RESONATORS FOR CIRCUIT QED

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Graphene, a single atomic layer from graphite [1], is an ideal candidate for nanoelectromechanical applications due to its large Young's modulus and low density. We have developed a micromanipulation technique to fabricate mechanical resonators [2, 3] out of suspended graphene. The fabrication steps are illustrated in Fig. 1a, where the graphene sheet is suspended using a PMMA stamp and positioned on top of a prefabricated gate electrode. The resonator is actuated with a high frequency ac signal applied to the gate, and the reflected sideband signal is detected to find the mechanical resonance [4] of the graphene (Fig. 1b).

Mechanical resonances of multilayer graphene and monolayer graphene samples have been detected. Fig. 2a shows the resonance frequency of a multilayer graphene sample with a biquadratic dependency on the DC bias voltage. The highest resonance frequency (~ 178 MHz) detected so far on monolayer ($L = \sim 0.5 \mu\text{m}$) graphene sample measured at 4 K is shown on Fig. 2b.

Further increase in frequency could be reached by utilizing a low-capacitance oscillator schematic (Fig. 1c). In this scheme, the electrical resonant circuit effectively eliminates the external wiring capacitances. Resonance at 6.7 GHz has been detected in such a scheme without graphene capacitor.

Our fully electrical detection method is applicable for nanoscale mechanical resonators in a large frequency range. The fabrication method is promising to build more complex nanoelectromechanical systems from graphene or carbon nanotubes [5].

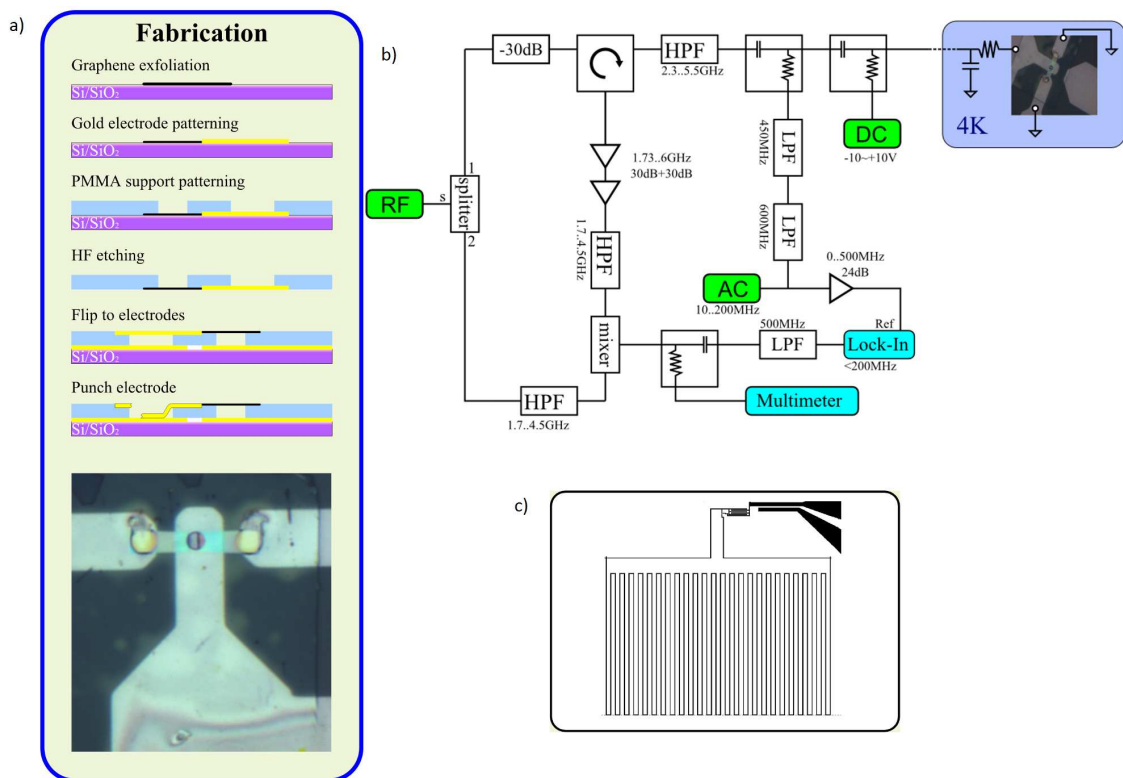


Figure 1: a) Fabrication steps of the graphene resonator. b) Reflection measurement scheme for sideband detection. c) Further increase in resonance frequency and Q value can be achieved using an on-chip LC circuit to eliminate wiring capacitances.

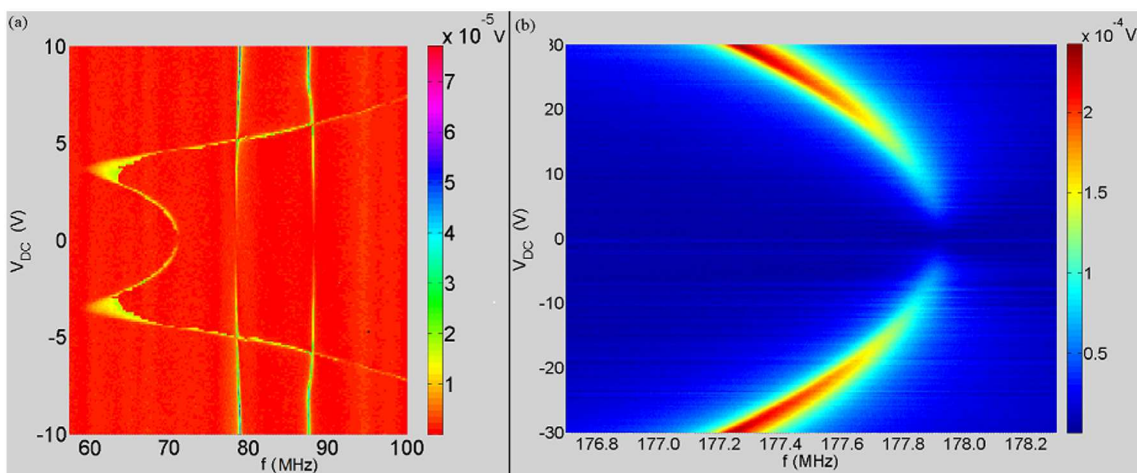


Figure 2: a) Biquadratic resonance versus gate voltage of a multilayer graphene resonator. b) Highest resonance frequency of a monolayer graphene resonator. Both samples were measured at 4 K.

References

- [1] K.S. Novoselov *et al.*, Science, 306 (2004) 666-669.
- [2] J. S. Bunch *et al.*, Science, 315 (2007) 490.
- [3] C. Changyao *et al.*, Nature Nanotechnology, 4 (2009) 861.
- [4] M.A. Sillanpää *et al.*, Appl. Phys. Lett., 95 (2009) 011909.
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